

Title (en)  
Semiconductor device and method of fabricating the same

Title (de)  
Halbleiterbauelement und Herstellungsverfahren dafür

Title (fr)  
Dispositif semi-conducteur et son procédé de fabrication

Publication  
**EP 1901349 A3 20131225 (EN)**

Application  
**EP 07022771 A 20041221**

Priority  
• EP 04808026 A 20041221  
• JP 2003428695 A 20031225  
• JP 2004107798 A 20040331

Abstract (en)  
[origin: US2005140007A1] A semiconductor device includes a base plate, and a semiconductor constituent body formed on the base plate. The semiconductor constituent body has a semiconductor substrate and a plurality of external connecting electrodes formed on the semiconductor substrate. An insulating layer is formed on the base plate around the semiconductor constituent body. A hard sheet is formed on the insulating layer. An interconnection is connected to the external connecting electrodes of the semiconductor constituent body.

IPC 8 full level  
**H01L 23/31** (2006.01); **H01L 23/16** (2006.01); **H01L 23/498** (2006.01); **H01L 23/538** (2006.01)

CPC (source: EP KR US)  
**H01L 23/12** (2013.01 - KR); **H01L 23/16** (2013.01 - EP US); **H01L 23/3121** (2013.01 - EP US); **H01L 23/3128** (2013.01 - EP US); **H01L 23/48** (2013.01 - KR); **H01L 23/5389** (2013.01 - EP US); **H01L 24/19** (2013.01 - EP US); **H01L 24/27** (2013.01 - EP US); **H01L 24/29** (2013.01 - EP US); **H01L 24/97** (2013.01 - EP US); **H01L 23/3114** (2013.01 - EP US); **H01L 23/49816** (2013.01 - EP US); **H01L 2224/0401** (2013.01 - EP US); **H01L 2224/04105** (2013.01 - EP US); **H01L 2224/12105** (2013.01 - EP US); **H01L 2224/20** (2013.01 - EP US); **H01L 2224/274** (2013.01 - EP US); **H01L 2224/32225** (2013.01 - EP US); **H01L 2224/73267** (2013.01 - EP US); **H01L 2224/82039** (2013.01 - EP US); **H01L 2224/83191** (2013.01 - EP US); **H01L 2224/92** (2013.01 - EP US); **H01L 2224/92244** (2013.01 - EP US); **H01L 2224/97** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01057** (2013.01 - EP US); **H01L 2924/01074** (2013.01 - EP US); **H01L 2924/01078** (2013.01 - EP US); **H01L 2924/09701** (2013.01 - EP US); **H01L 2924/10253** (2013.01 - EP US); **H01L 2924/12042** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/15311** (2013.01 - EP US); **H01L 2924/15787** (2013.01 - EP US); **H01L 2924/3511** (2013.01 - EP)

Citation (search report)  
• [XA] JP 2000124363 A 20000428 - CITIZEN ELECTRONICS  
• [IA] EP 0865082 A1 19980916 - HITACHI LTD [JP]  
• [XA] US 2002144775 A1 20021010 - TUNG I-CHUNG [TW], et al  
• [A] US 2002108768 A1 20020815 - JIMAREZ LISA J [US], et al  
• [A] US 2001010627 A1 20010802 - AKAGAWA MASATOSHI [JP]

Designated contracting state (EPC)  
BE DE FI FR GB

Designated extension state (EPC)  
AL BA HR LV MK

DOCDB simple family (publication)  
**US 2005140007 A1 20050630**; **US 7489032 B2 20090210**; DE 602004021927 D1 20090820; EP 1629533 A2 20060301; EP 1629533 B1 20090708; EP 1901349 A2 20080319; EP 1901349 A3 20131225; HK 1095208 A1 20070427; KR 100731842 B1 20070625; KR 20060028748 A 20060331; TW 200527647 A 20050816; TW I250636 B 20060301; US 2008014681 A1 20080117; US 7867828 B2 20110111; WO 2005064641 A2 20050714; WO 2005064641 A3 20051117

DOCDB simple family (application)  
**US 1813804 A 20041220**; DE 602004021927 T 20041221; EP 04808026 A 20041221; EP 07022771 A 20041221; HK 07102410 A 20070305; JP 2004019675 W 20041221; KR 20067001723 A 20060125; TW 93139944 A 20041222; US 78258707 A 20070724